

# **isc Silicon NPN RF Transistor**

# 2SC4197

#### DESCRIPTION

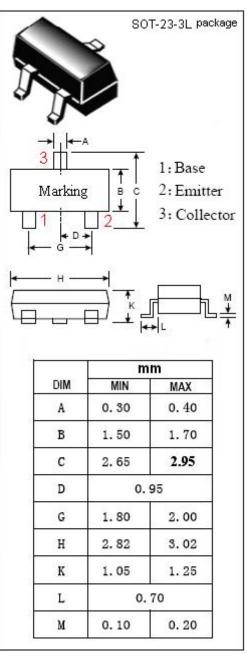
- Low Noise
- High Gain Bandwidth Product
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

 Designed for UHF frequency converter, wide band amplifier applications.

| ABSOLUTE MAXIMUM RATINGS(Ta=25°C) |
|-----------------------------------|
|-----------------------------------|

| SYMBOL           | PARAMETER                               | VALUE   | UNIT |
|------------------|---|---------|------|
| V <sub>CBO</sub> | Collector-Base Voltage                  | 25      | V    |
| Vceo             | Collector-Emitter Voltage               | 13      | V    |
| V <sub>EBO</sub> | Emitter-Base Voltage                    | 3       | V    |
| lc               | Collector Current-Continuous            | 50      | mA   |
| Pc               | Collector Power Dissipation<br>@Tc=25°C | 0.15    | W    |
| TJ               | Junction Temperature                    | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature Range               | -55~150 | °C   |



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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS   | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V <sub>(BR)CBO</sub> | Collector-Base Breakdown Voltage     | I <sub>C</sub> = 10 μ A ; I <sub>E</sub> = 0                               | 25  |      |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 20mA ; I <sub>B</sub> = 4mA                               |     |      | 0.3 | V    |
| Ісво                 | Collector Cutoff Current             | V <sub>CB</sub> = 15V; I <sub>E</sub> = 0                                  |     |      | 0.1 | μA   |
| I <sub>CEO</sub>     | Collector Cutoff Current             | $V_{CE}$ = 13V; $R_{BE}$ = $\infty$  |     |      | 10  | μA   |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = 3V; I <sub>C</sub> = 0                                   |     |      | 0.3 | μA   |
| hfe                  | DC Current Gain                      | Ic= 5mA ; Vce= 5V  | 50  |      | 180 |      |
| f <sub>T</sub>       | Current-Gain—Bandwidth Product       | I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 5V                               | 3.0 | 3.8  |     | GHz  |
| Сов                  | Output Capacitance                   | I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz                       |     | 0.85 | 1.3 | pF   |
| CG                   | Conversion Gain                      | I <sub>c</sub> = 0.8mA ; V <sub>cc</sub> = 5V;<br>f <sub>in</sub> = 900MHz |     | 19   |     | dB   |
| NF                   | Noise Figure                         | f <sub>osc</sub> = 930MHz(-5dB),<br>f <sub>out</sub> = 30MHz               |     | 8    |     | dB   |

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